



### N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C	
30V	$6m\Omega$ @ $V_{GS} = 10V$		
	10mΩ @ V <sub>GS</sub> = 4.5V	55.6A	

### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Excellent  $Q_{GD} \times R_{DS(ON)}$  Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

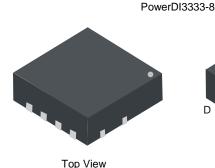
## **Description and Applications**

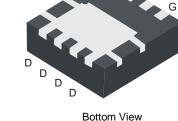
This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

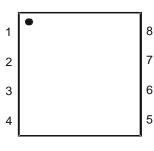
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

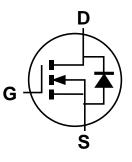
### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)









Top View

**Equivalent Circuit** 

### Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3006LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT3006LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <a href="https://www.diodes.com/design/support/packaging/diodes-packaging/">https://www.diodes.com/design/support/packaging/diodes-packaging/</a>.
   <a href="https://www.diodes.com/design/support/packaging/diodes-packaging/">https://www.diodes.com/design/support/packaging/diodes-packaging/</a>.

## **Marking Information**



SK1 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V	
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	55.6 44.4	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	16.0 12.8	А	
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	2	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	80	Α	
Avalanche Current, L=0.1mH	I <sub>AS</sub>	25	Α	
Avalanche Energy, L=0.1mH	E <sub>AS</sub>	31	mJ	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	$P_{D}$	27.8	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	4.5	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	54	C/VV
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C	

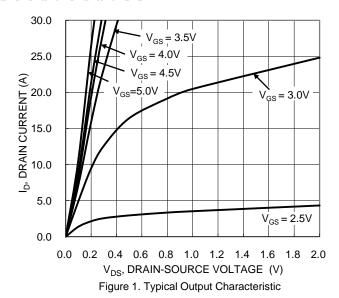
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

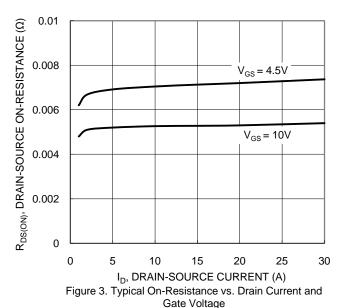
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = +20V, V <sub>DS</sub> = 0V V <sub>GS</sub> = -16V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	4.8	6	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A	
Static Diani-Source Off-Resistance	R <sub>DS(ON)</sub>	_	6.9	10		$V_{GS} = 4.5V, I_D = 12A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 2A$	
DYNAMIC CHARACTERISTICS (Note 8)	<u>.                                      </u>					•	
Input Capacitance	C <sub>iss</sub>	_	1,155	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	456	_			
Reverse Transfer Capacitance	C <sub>rss</sub>	_	72	_			
Gate Resistance	$R_{G}$	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	16.7	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	8.4	_		V <sub>DD</sub> = 15V, I <sub>D</sub> = 9A	
Gate-Source Charge	Q <sub>GS</sub>	_	2.2	_	nC		
Gate-Drain Charge	$Q_GD$	_	3.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.5	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 9A$	
Turn-On Rise Time	t <sub>R</sub>	_	5.5	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	13.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	4.6	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	19.3	_	ns	1. 1.54 11/11 1004/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	8.6	_	nC	$I_F = 1.5A$ , di/dt = 100A/ $\mu$ s	

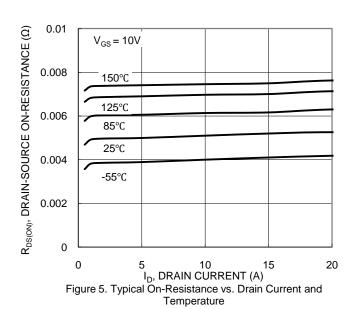
Notes: 5. R<sub>0</sub>JA is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. R<sub>0</sub>JC is guaranteed by design while R<sub>0</sub>JA is determined by the user's board design.

- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.









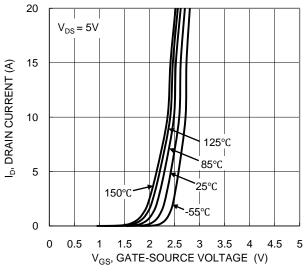


Figure 2. Typical Transfer Characteristic

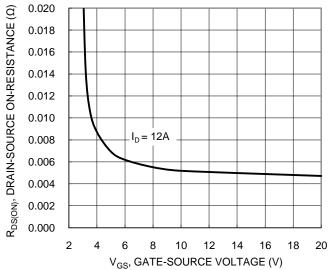


Figure 4. Typical Transfer Characteristic

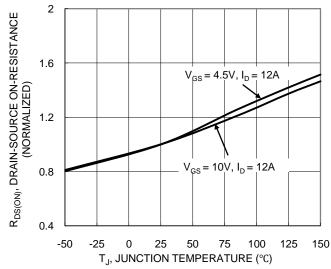


Figure 6. On-Resistance Variation with Temperature



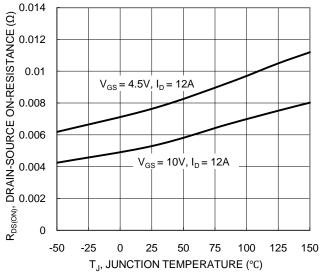
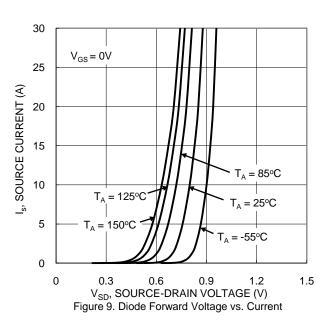
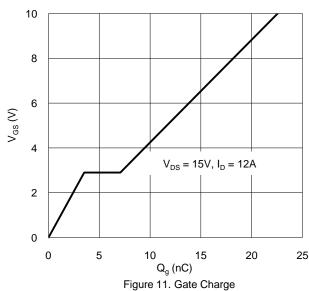


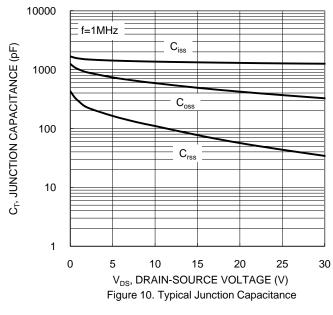
Figure 7. On-Resistance Variation with Temperature

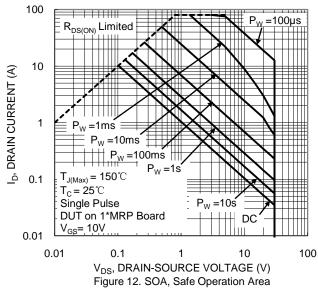




2.4  $V_{\text{GS(TH)}}$ , GATE THRESHOLD VOLTAGE (V) 2.2 2 1.8  $I_D = 1 \text{mA}$ 1.6 1.4  $I_{D} = 250 \mu A$ 1.2 1 0.8 0.6 0.4 -50 -25 0 25 50 75 100 125 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature







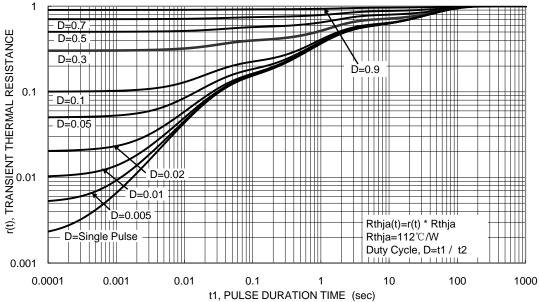


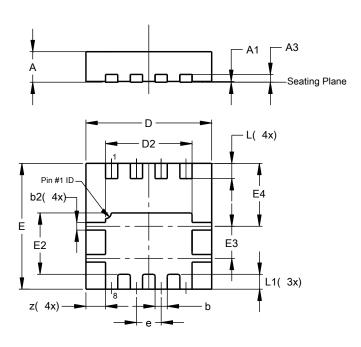
Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8

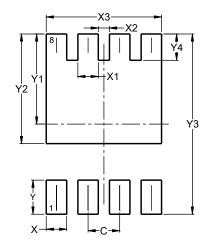


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
А3	1	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	_	0.515			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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